

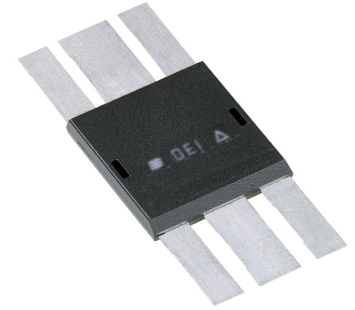
## Silicon Carbide Schottky Diode

$V_{RRM} = 600\text{ V}$

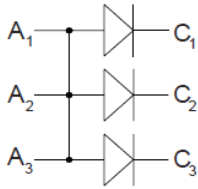
$I_{F(AVG)} = 10\text{ A}$

$C_J = 120\text{ pF}$

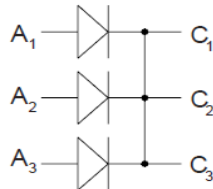
Part Number	$V_{RRM}$ (V)	$I_{F(AVG)}$ (A)	Configuration
SS150TA60110	600	10	Triple Common Anode
SS150TC60110	600	10	Triple Common Cathode
SS150TI60110	600	10	Triple Independent



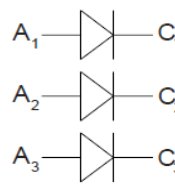
Triple Anode (TA)



Triple Cathode (TC)



Triple Independent (TI)



A = Anode C = Cathode

Symbol	Parameter per diode	Test Conditions	Maximum Ratings	Features
$V_{RRM}$	Repetitive Peak Reverse Voltage		600 V	<ul style="list-style-type: none"> <li>600 V SiC Schottky Diode</li> <li>Surface Mount Package</li> <li>Zero Reverse Recovery</li> <li>Zero Forward Recovery</li> <li>High Frequency Operation</li> <li>Temperature Independent Behavior</li> <li>Positive Temperature Coefficient for <math>V_F</math></li> </ul>
$V_{RSM}$	Repetitive Surge Reverse Voltage		600 V	
$V_{DC}$	DC Blocking Voltage		600 V	
$I_{F(AVG)}$	Average Forward Current	$T_J = 175^\circ\text{C}$	10 A	
$I_{FRM}$	Repetitive Peak Forward Surge Current	$T_C = 25^\circ\text{C}$ , $t_p = 10\text{ ms}$ Half Sine Wave	67 A	
$I_{FSM}$	Non-Repetitive Peak Forward Surge Current	$T_C = 25^\circ\text{C}$ , $t_p = 10\ \mu\text{s}$ Pulse	250 A	
$T_{VJ}$	Operating Virtual Junction Temperature		-55 to +175 °C	
$T_{STG}$	Storage Temperature		-55 to +175 °C	
$P_{TOT}$	$T_C = 25^\circ\text{C}$ (30 W/ per diode)		90 W	

### Features

- 600 V SiC Schottky Diode
- Surface Mount Package
- Zero Reverse Recovery
- Zero Forward Recovery
- High Frequency Operation
- Temperature Independent Behavior
- Positive Temperature Coefficient for  $V_F$

### Applications

- MHz Switch Mode Power Supplies
- High Frequency Converters
- Resonant Converters
- Rectifier Circuits

Symbol	Parameter	Test Conditions	Characteristic Values		
			Typ.	Max.	Units
$T_J = 25^\circ\text{C}$ unless otherwise specified					
$V_F$	Forward Voltage	$I_F = 5\text{ A}$ , $T_J = 25^\circ\text{C}$ $T_J = 175^\circ\text{C}$	1.7 2.2	2 2.5	V
$I_R$	Reverse Current	$V_R = 600\text{ V}$ , $T_J = 25^\circ\text{C}$ $T_J = 175^\circ\text{C}$	10 20	50 200	$\mu\text{A}$
$C_J$	Junction Capacitance	$f = 1\text{ MHz}$ , $V_R = 0\text{ V}$ $V_R = 200\text{ V}$ $V_R = 600\text{ V}$	600 130 120		pF
$Q_C$	Capacitive Charge	$V_R = 600\text{ V}$	72		nC
$R_{THJC}$	Thermal Resistance		1.7		$^\circ\text{C/W}$
$T_L$	Lead Soldering Temperature	1.6 mm (0.063 in) from case for 10 s	300		$^\circ\text{C}$
<b>Isolation</b>	Pin to Substrate Pin to Pin		>1800 >1500		$V_{RMS}$
<b>Weight</b>			2		g

Fig. 1

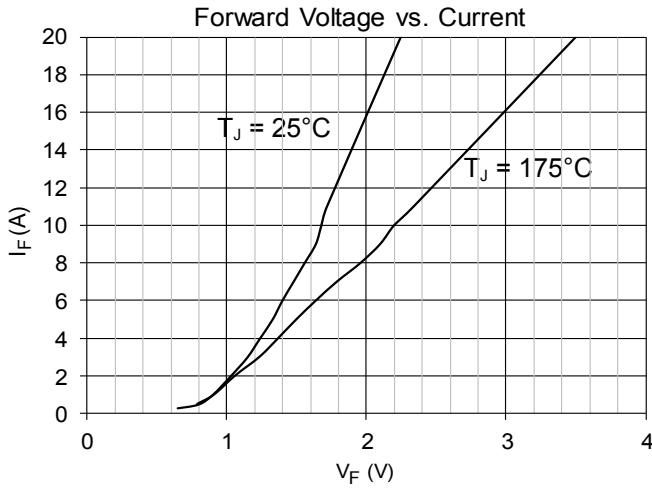


Fig. 2

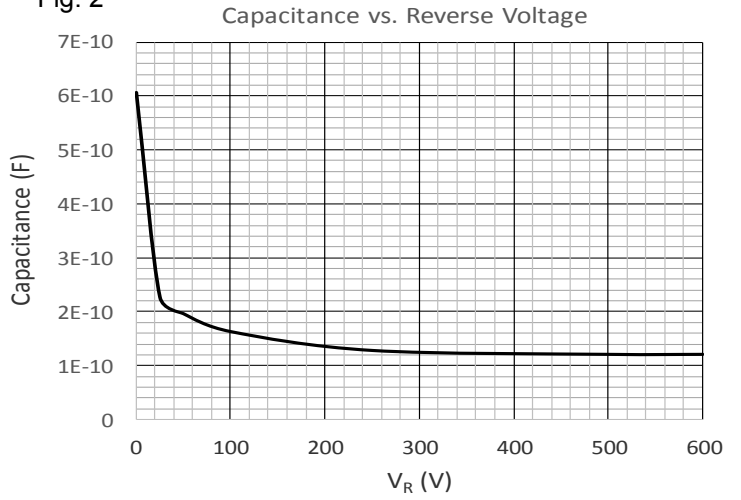


Fig. 3

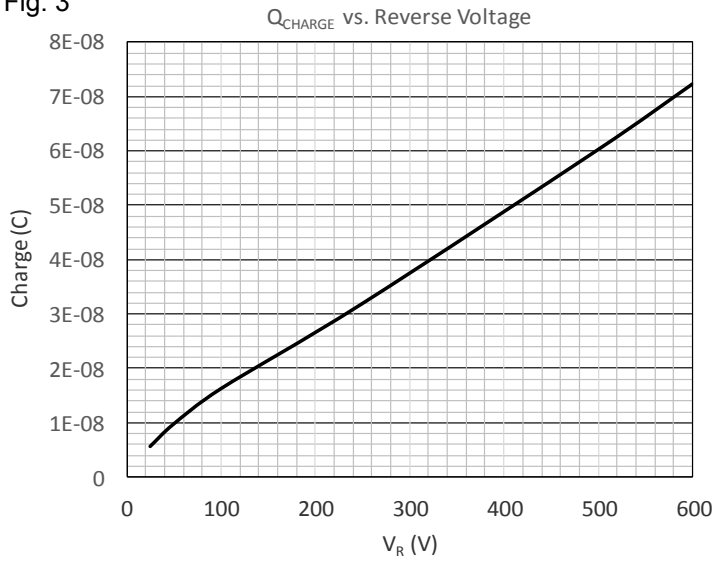


Fig. 4

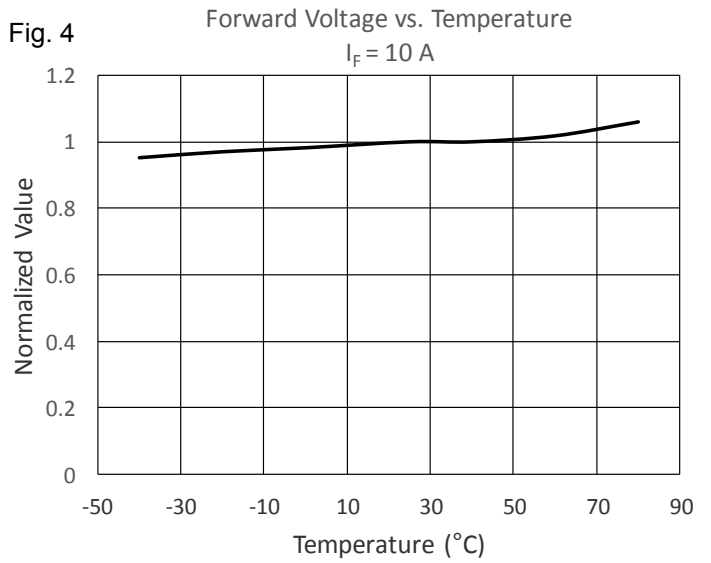


Fig. 5

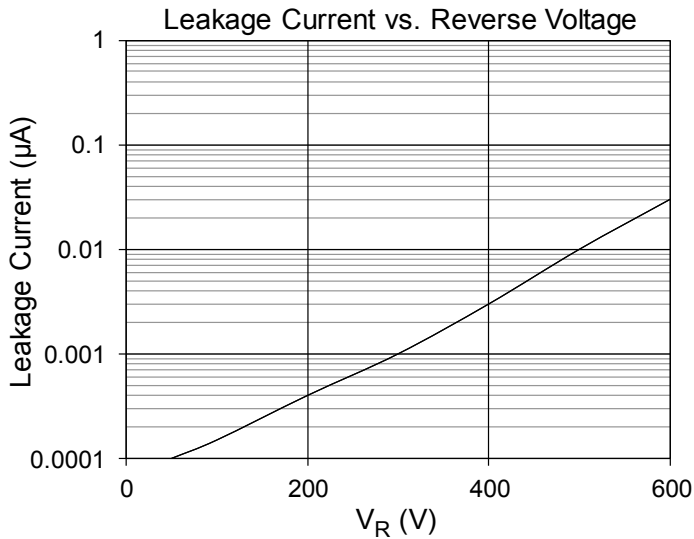


Fig. 6

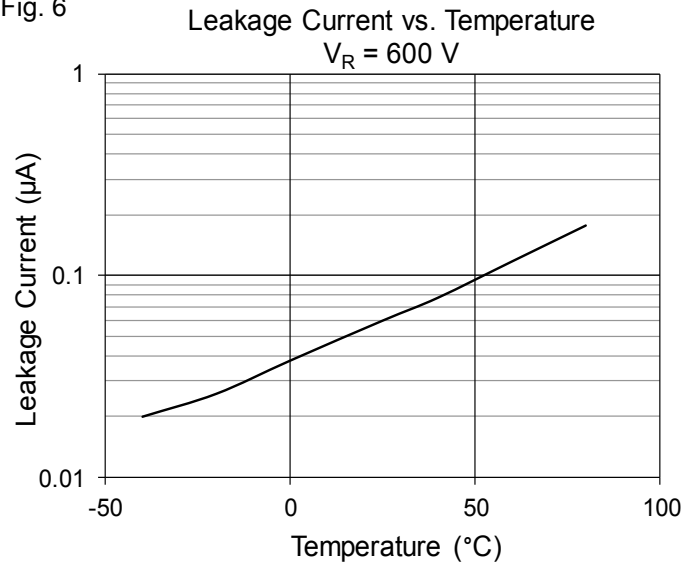
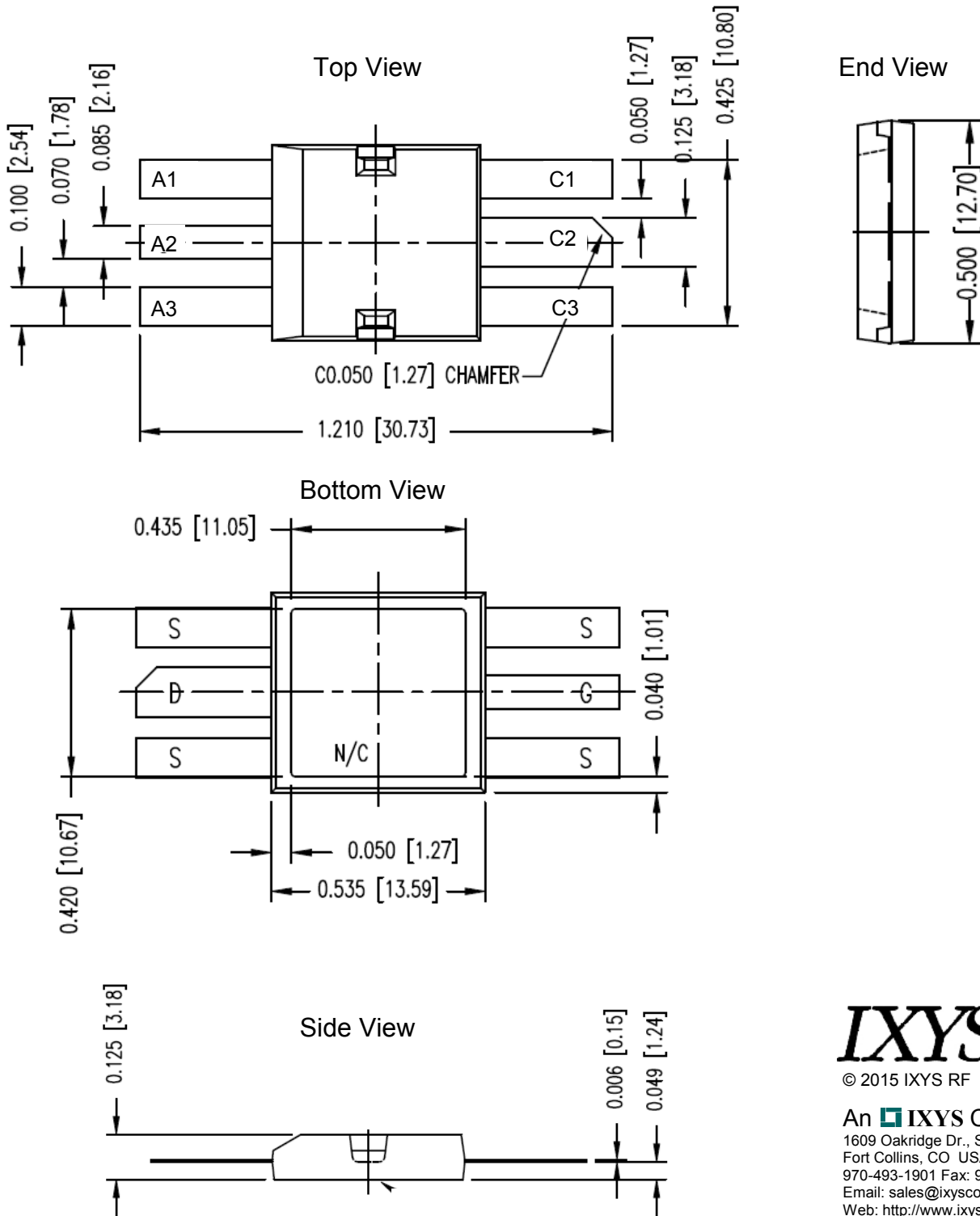


Fig. 7 Package Diagram



DCB – Direct Copper Bond under Nickel plate on an Aluminum Nitride substrate, electrically isolated from any pin.